## SILICON EPITAXIAL PLANAR DIODE

## Band Swithing Diode

## Features

- Extremely small surface mounting type
- High reliability


## Applications

- High frequency switching

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 35 | V |
| Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 100 | mA |
| Junction Temperature | $\mathrm{T}_{J}$ | 125 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | -55 to +125 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Max. | Unit |
| :---: | :---: | :---: | :---: |
| Forward Voltage <br> at $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | 1 | V |
| Reverse Current <br> at $\mathrm{V}_{\mathrm{R}}=25 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | 10 | nA |
| Capacitance Between Terminals <br> at $\mathrm{V}_{\mathrm{R}}=6 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\mathrm{T}}$ | 1.2 | pF |
| Forward Operating Resistance <br> at $\mathrm{I}_{\mathrm{F}}=2 \mathrm{~mA}, \mathrm{f}=100 \mathrm{MHz}$ | $\mathrm{R}_{\mathrm{F}}$ | 0.7 | $\Omega$ |



Fig. 1 Forward characteristics


Fig. 2 Reverse characteristics



Fig. 3 Capacitance between terminals characteristics


Fig. 4 Forward operating resistance characteristics

## PACKAGE OUTLINE



| UNIT | A | $\mathrm{b}_{\mathrm{p}}$ | C | D | E | $\mathrm{H}_{\mathrm{E}}$ | V | $\angle$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| mm | 0.70 | 0.4 | 0.135 | 1.25 | 0.85 | 1.7 | 0.1 | $5^{\circ}$ |
|  | 0.60 | 0.3 | 0.127 | 1.15 | 0.75 | 1.5 |  |  |

